

FEATURES

- 10µs Short Circuit Withstand
- Non Punch Through Silicon
- Isolated Cu Base with Al₂O₃ Substrates
- Lead Free construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 600V to 3300V and currents up to 2400A.

The DIM600DDS12-A000 is a dual switch 1200V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM600DDS12-A000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	1200V
$V_{CE(sat)}$ * (typ)	2.2 V
I_C (max)	600A
$I_{C(PK)}$ (max)	1200A

* Measured at the power busbars, not the auxiliary terminals

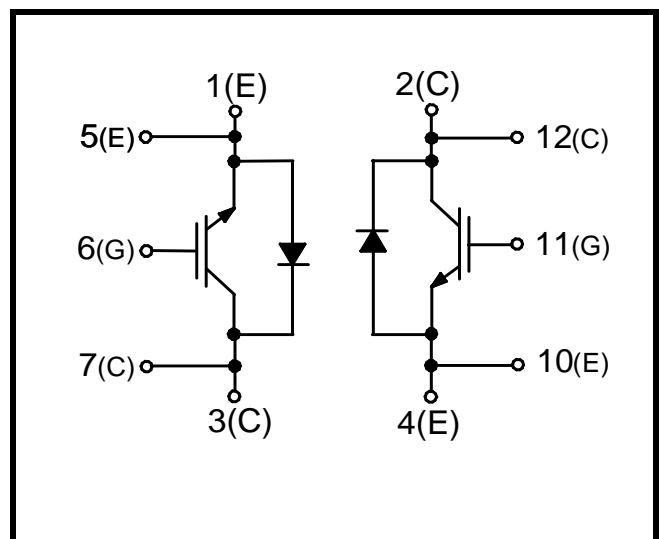
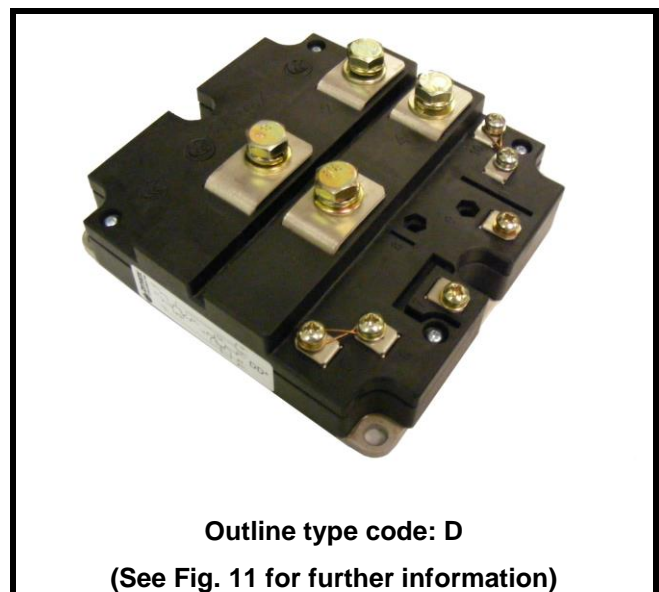


Fig. 1 Circuit configuration



Outline type code: D

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	1200	V
V_{GES}	Gate-emitter voltage		± 20	V
I_C	Continuous collector current	$T_{case} = 85^{\circ}\text{C}$	600	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 115^{\circ}\text{C}$	1200	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	5208	W
I^2t	Diode I^2t value	$V_R = 0$, $t_p = 10\text{ms}$, $T_j = 125^{\circ}\text{C}$	100	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	Al_2O_3
Baseplate material:	Cu
Creepage distance:	20mm
Clearance:	10mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor (per switch)	Continuous dissipation - junction to case	-	-	24	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode (per switch)	Continuous dissipation - junction to case	-	-	40	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS
T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}			1	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C			18	mA
I _{GES}	Gate leakage current	V _{GE} = ± 20V, V _{CE} = 0V			3	µA
V _{GE(TH)}	Gate threshold voltage	I _C = 20mA, V _{GE} = V _{CE}	4.5	5.5	6.5	V
V _{CE(sat)}	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 400A		2.2	2.8	V
		V _{GE} = 15V, I _C = 400A, T _j = 125°C		2.6	3.2	V
I _F	Diode forward current	DC			600	A
I _{FM}	Diode maximum forward current	t _p = 1ms			1200	A
V _F	Diode forward voltage	I _F = 400A		2.1	2.4	V
		I _F = 400A, T _j = 125°C		2.1	2.4	V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		70		nF
Q _g	Gate charge	±15V		6		µC
C _{res}	Reverse transfer capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz				nF
L _M	Module inductance – per switch			20		nH
R _{INT}	Internal transistor resistance – per switch			270		µΩ
SC _{Data}	Short circuit current, I _{SC}	T _j = 125°C, V _{CC} = 900V t _p ≤ 10µs, V _{GE} ≤ 15V V _{CE(max)} = V _{CES} – L* x di/dt IEC 60747-9		3400		A

Note:

 * L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 600\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(ON)} = 2.7\Omega$ $R_{G(OFF)} = 2.7\Omega$ $L_S \sim 120\text{nH}$		920		ns
t_f	Fall time			140		ns
E_{OFF}	Turn-off energy loss			100		mJ
$t_{d(on)}$	Turn-on delay time			390		ns
t_r	Rise time			180		ns
E_{ON}	Turn-on energy loss			55		mJ
Q_{rr}	Diode reverse recovery charge		$I_F = 600\text{A}$ $V_{CE} = 600\text{V}$ $di_F/dt = 3600\text{A}/\mu\text{s}$		100	
I_{rr}	Diode reverse recovery current			370		A
E_{rec}	Diode reverse recovery energy			50		mJ

$T_{case} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 600\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(ON)} = 2.7\Omega$ $R_{G(OFF)} = 2.7\Omega$ $L_S \sim 120\text{nH}$		1000		ns
t_f	Fall time			160		ns
E_{OFF}	Turn-off energy loss			125		mJ
$t_{d(on)}$	Turn-on delay time			460		ns
t_r	Rise time			180		ns
E_{ON}	Turn-on energy loss			65		mJ
Q_{rr}	Diode reverse recovery charge		$I_F = 600\text{A}$ $V_{CE} = 600\text{V}$ $di_F/dt = 3600\text{A}/\mu\text{s}$		200	
I_{rr}	Diode reverse recovery current			480		A
E_{rec}	Diode reverse recovery energy			100		mJ

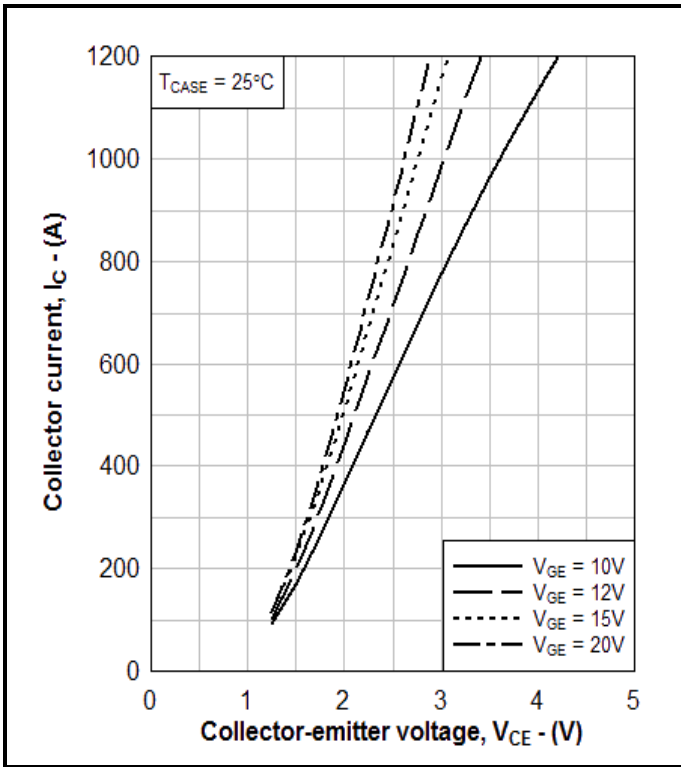


Fig. 3 Typical output characteristics

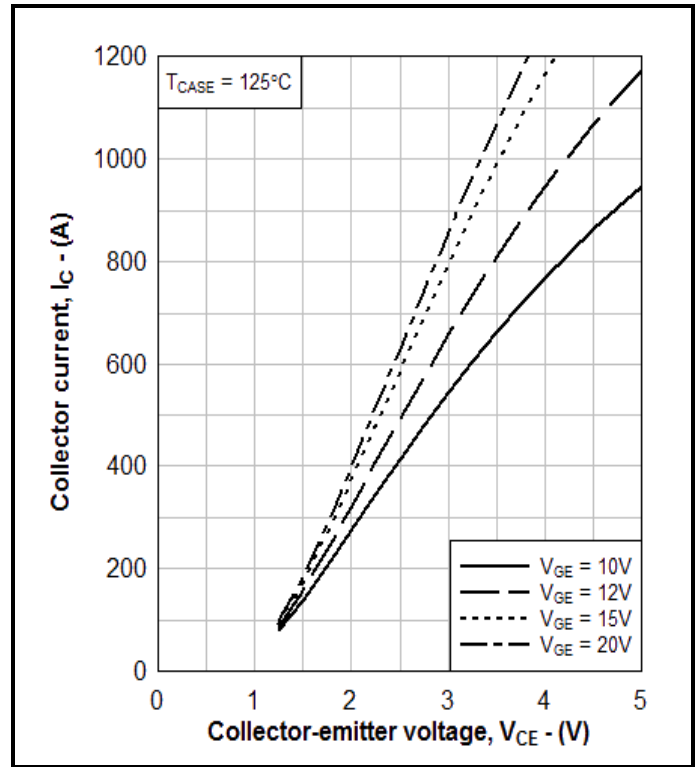


Fig. 4 Typical output characteristics

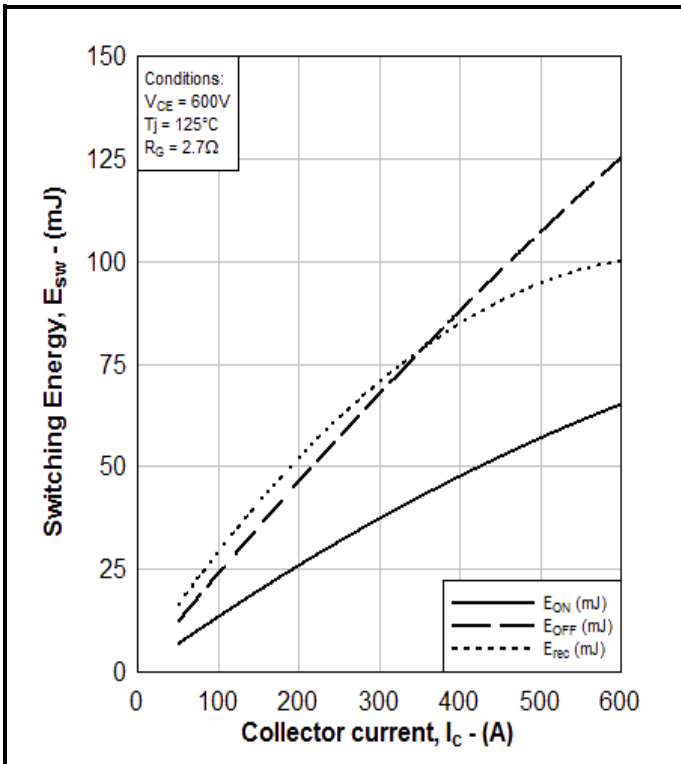


Fig. 5 Typical switching energy vs collector current

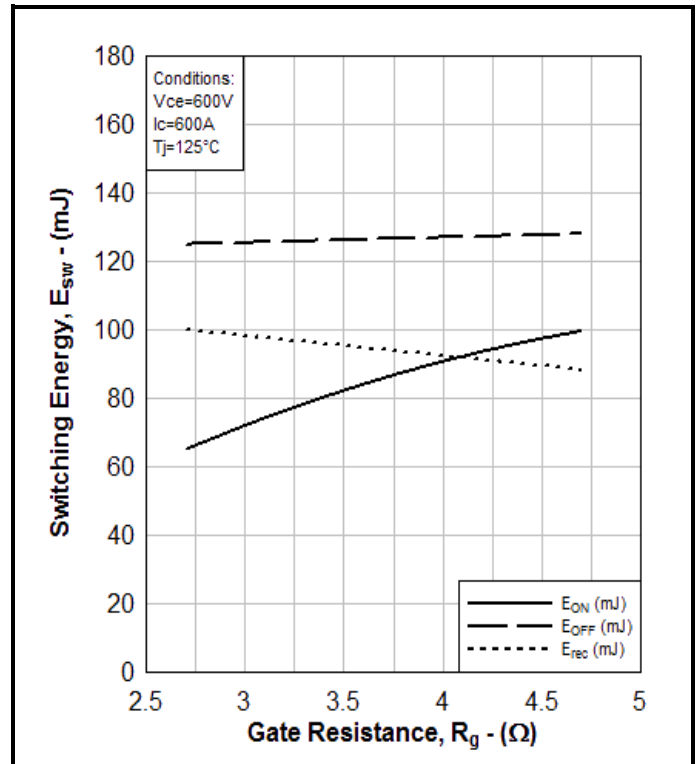


Fig. 6 Typical switching energy vs gate resistance

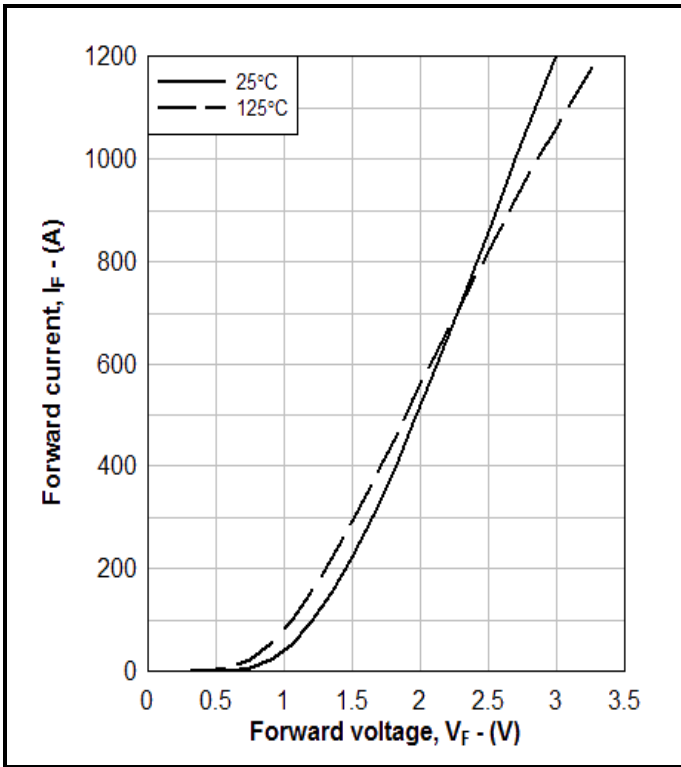


Fig. 7 Diode typical forward characteristics

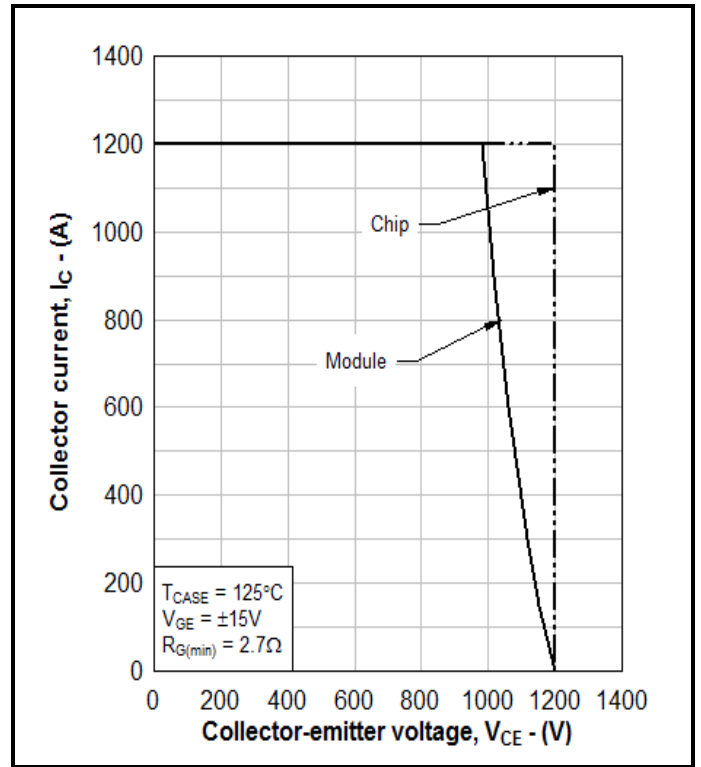


Fig. 8 Reverse bias safe operating area

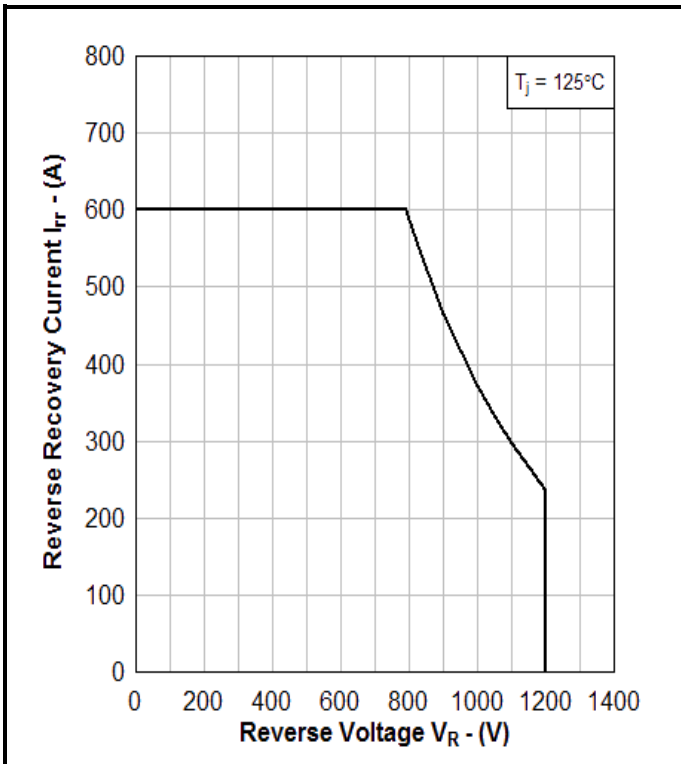


Fig. 9 Diode reverse bias safe operating area

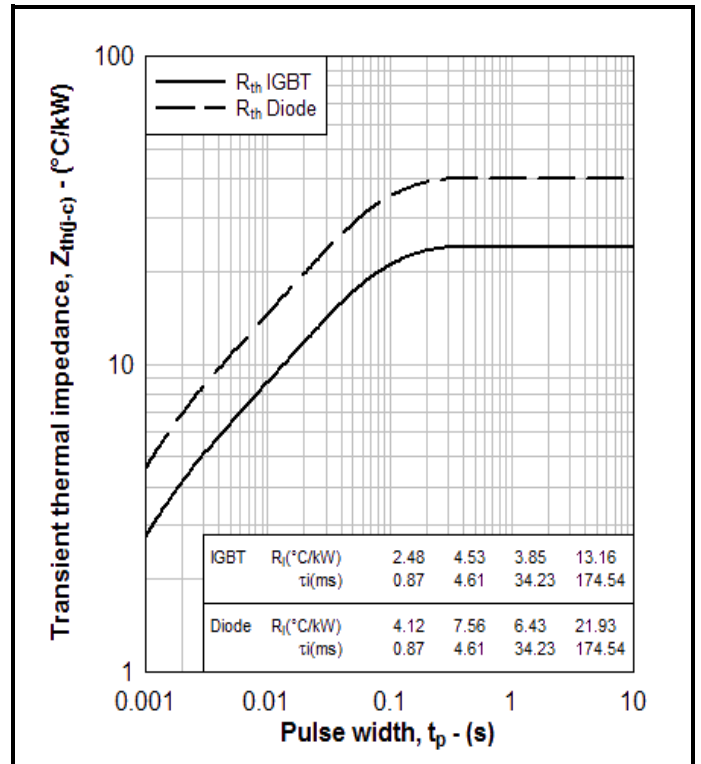
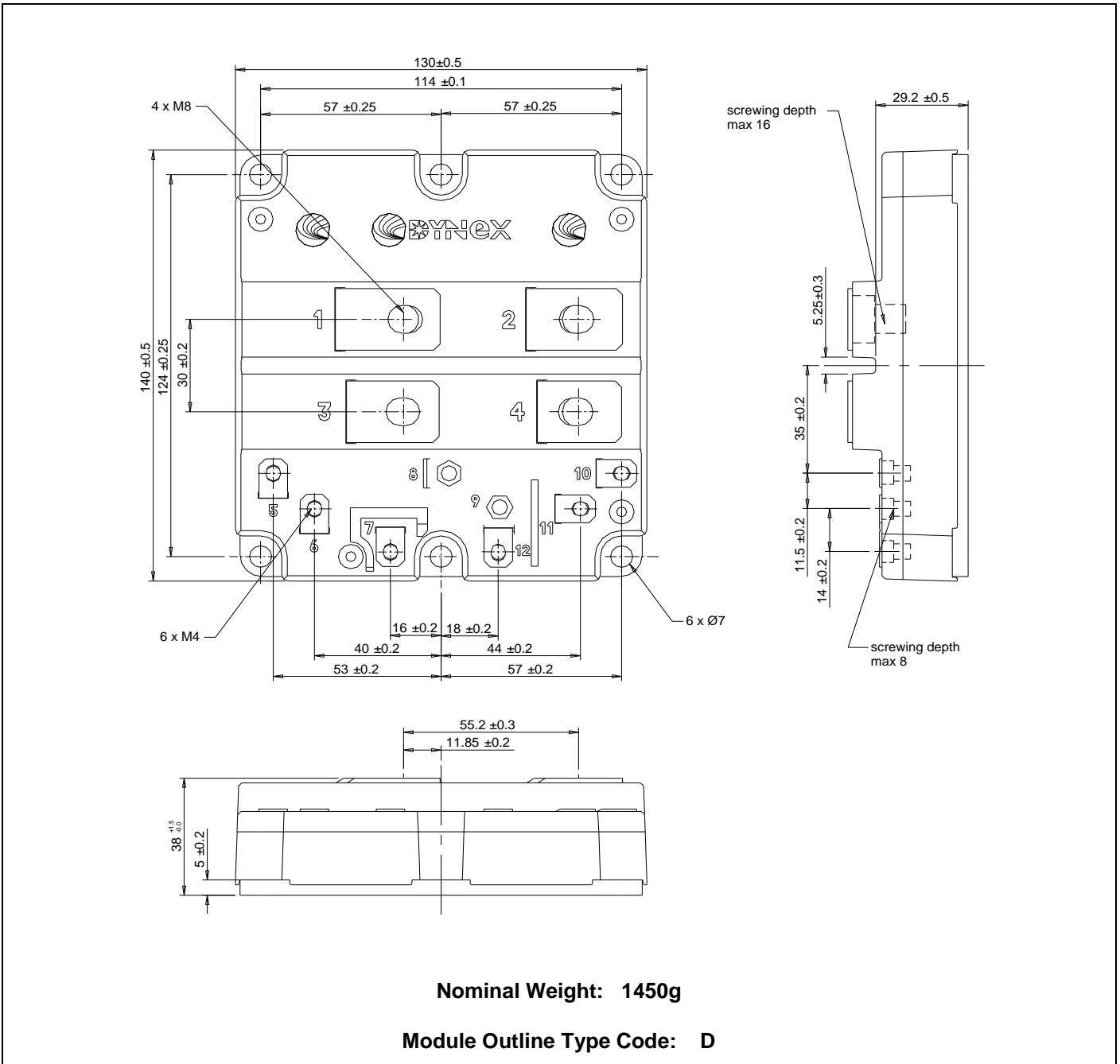


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 1450g

Module Outline Type Code: D

Fig. 11 Module outline drawing

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